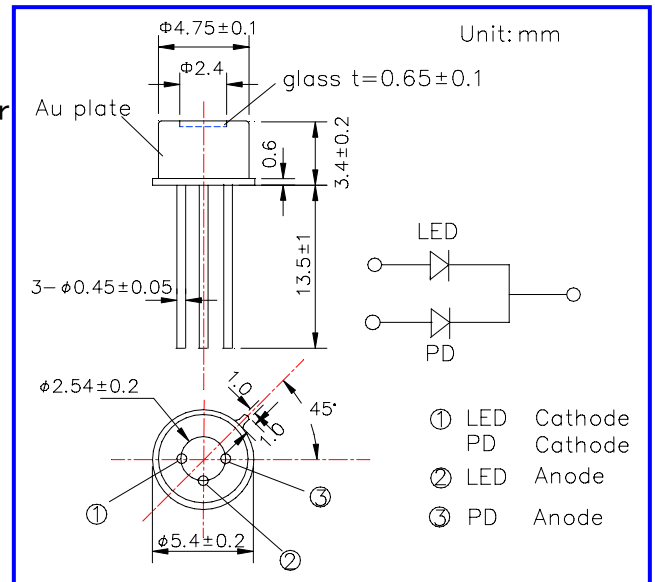


LN850/PD010-40D52 metal can sealed PD monitoring high power LED

LN850/PD010-40D52 consists of a GaAlAs LED 850nm and a Si-PD mounted on TO-18 stem hermetically sealed with a glass flat can, and is designed to monitor reflected light through detector for controlling its own output power

◆Outer dimension (Unit: mm)



◆Specifications

- 1) Product Name LED Lamp with PD Monitor
- 2) Type No. LN850/PD010-40D52
- 3) Chip
 - (1) Chip material GaAlAs, Si (PIN)
 - (2) Peak wavelength 850nm
- 4) Package
 - (1) Stem TO-18
 - (2) Lens Φ2.4 Flat Glass
 - (3) Can Metal Can (Gold Plate)

◆Absolute Maximum Ratings Ta=25°C

Device	Item	Symbol	Maximum Rated	Unit
LED	Power Dissipation	PD	160	mW
LED	Forward Current	IF	100	mA
LED	Pulse Forward Current	IFP	1	A
LED	Reverse Voltage	VR	5	V
PD	Reverse Voltage	VR	100	V
	Operating Temperature	TOPR	-30 ~ +85	°C
	Storage Temperature	TSTG	-30 ~ +100	°C
	Soldering Temperature	TSOL	260	°C

‡Pulse Forward Current condition : duty=1% and tw=10 μ s.

‡Soldering condition : Soldering condition must be completed within 3 seconds at 260°C

◆Electro-Optical Characteristics Ta=25°C

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.50	1.70	V
Reverse Current	IR	VR=5V			10	μ A
Total Radiated Power	PO	IF=50mA	3.0	6.0		mW
Radiant Intensity	IE	IF=50mA	2.5	5.0		mW/sr
Peak Wavelength	λ P	IF=50mA	840	850	860	nm
Half Width	Δλ	IF=50mA		35		nm
Viewing Half Angle	Δθ	IF=50mA		±55		deg.
Rise Time	tr	IF=50mA		60		ns
Fall Time	tf	IF=50mA		40		ns
Output Current	IL	VR=0V	130	270		μ A
Dark Current	ID	VR=10V			10	nA

‡Total Radiated Power is measured by Photodyne #500.

‡Radiant Intensity is measured by Tektronix J-6512